

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Pravin K. Narwankar, et al.

Serial No. 10/772,893

Filed: February 4, 2004

For: Tailoring Nitrogen Profile In Silicon
Oxynitride Using Rapid Thermal
Annealing With Ammonia Under
Ultra-Low Pressure

) Examiner: Unassigned

) Art Unit: Unassigned

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

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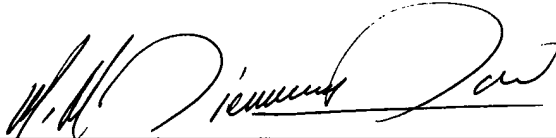
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If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: March 10, 2004



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Substitute for Form 1449/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/772,893		
		Filing Date	02/04/04		
		First Named Inventor:	Pravin K. Narwankar		
		Art Unit	Unassigned		
		Examiner Name	Unassigned		
		Attorney Docket Number	008209/USA/FEP/GCM/RKK		
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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		ITO, T., et al., "Direct Thermal Nitridation of Silicon Dioxide Films In Anhydrous Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Optical Properties, Vol. 127, No. 9, September 1980, pages 2053-2057,	
		ITO, T., et al., "Retardation of Destructive Breakdown of SiO ₂ Films Annealed in Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Ammonia Gas, Vol. 127, No. 10, September 1980, pages 2248-2251,	
		LEK, C. M., et al., "Impact of Decoupled Plasma Nitridation of Ultra-Thin Gate Oxide on the Performance of P-Channel MOSFETs," Institute of Physics Publishing, Semicond. Sci. Technol., Vol. 17, 2002, pages L25-L28.	

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